

DB101G~DB107G

Single-Phase Glass Passivated Silicon Bridge Rectifier

Reverse Voltage - 50 to 1000 V

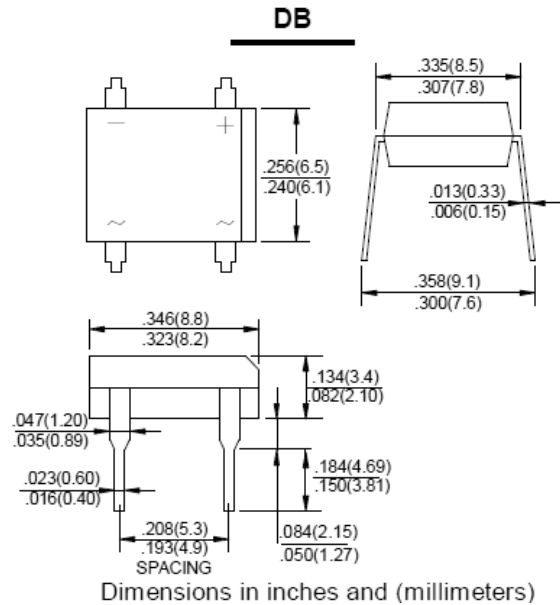
Forward Current - 1 A

Features

- Glass passivated chip junction
- Ideal for printed circuit board
- Low forward voltage drop, high current capability

Mechanical Data

- Case: Molded plastic, DB
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026
- Mounting position: Any



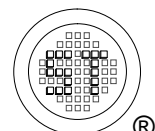
Absolute Maximum Ratings and Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbols	DB101G	DB102G	DB103G	DB104G	DB105G	DB106G	DB107G	Units
	Marking	DB101G	DB102G	DB103G	DB104G	DB105G	DB106G	DB107G	-
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_a = 40^\circ\text{C}$	$I_{(AV)}$	1							A
Peak Forward Surge Current 8.3 ms Single Half-sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	50							A
Maximum Forward Voltage at 1 A	V_F	1.1							V
Maximum Reverse Current at Rated DC Blocking Voltage	I_R	10 500							μA
		at $T_j = 25^\circ\text{C}$ at $T_j = 125^\circ\text{C}$							
I^2t Rating for Fusing ($t < 8.3$ ms)	I^2t	10.4							A^2s
Typical Junction Capacitance ¹⁾	C_J	25							pF
Typical Thermal Resistance ²⁾	$R_{\theta JA}$	40							$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150							$^\circ\text{C}$

¹⁾ Measured at 1 MHz and applied reverse voltage of 4 V.

²⁾ Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B with 0.5 X 0.5" (13 X 13 mm) copper pads.



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Electrical characteristic curves

